

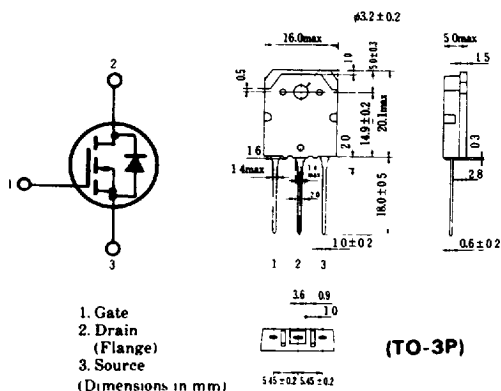
SILICON N-CHANNEL MOS FET

HIGH SPEED POWER SWITCHING, HIGH FREQUENCY POWER AMPLIFIER

Complementary pair with 2SJ114

■ FEATURES

- Low On-Resistance.
- High Speed Switching.
- High Cutoff Frequency.
- No Secondary Breakdown.
- Suitable for Switching Regulator, DC-DC Converter, RF Amplifiers, and Ultrasonic Power Oscillators.

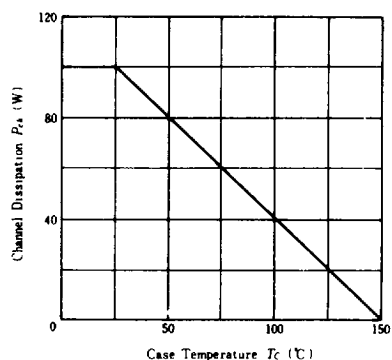


■ **ABSOLUTE MAXIMUM RATINGS** ($T_a=25^\circ\text{C}$)

Item	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	200	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current	I_D	8	A
Drain Peak Current	$I_{D(peak)}$	12	A
Body-Drain Diode Reverse Drain Current	I_{OR}	8	A
Channel Dissipation	P_{ch}^*	100	W
Channel Temperature	T_{ch}	150	°C
Storage Temperature	T_{stg}	-55 ~ +150	°C

* Value at $T_c = 25^\circ\text{C}$

POWER VS. TEMPERATURE DERATING



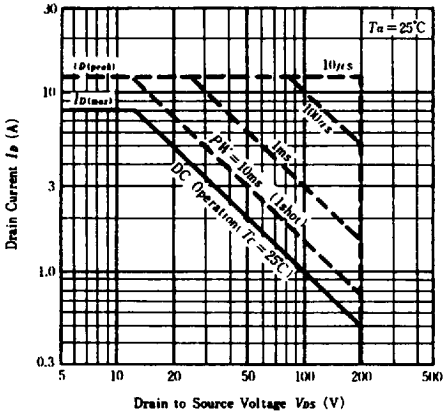
■ ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$)

Item	Symbol	Test Condition	min.	typ.	max.	Unit
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D=10\text{mA}$, $V_{GS}=0$	200	—	—	V
Gate-Source Leak Current	I_{GSS}	$V_{GS}=\pm 20\text{V}$, $V_{DS}=0$	—	—	± 1	μA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=160\text{V}$, $V_{GS}=0$	—	—	1	mA
Gate-Source Cutoff Voltage	$V_{GS(off)}$	$I_D=1\text{mA}$, $V_{DS}=10\text{V}$	2.0	—	5.0	V
Static Drain-Source On State Resistance	$R_{DS(on)}$	$I_D=4\text{A}$, $V_{GS}=15\text{V}^*$	—	0.5	0.7	Ω
Drain-Source Saturation Voltage	$V_{DS(on)}$	$I_D=4\text{A}$, $V_{GS}=15\text{V}^*$	—	2.0	2.8	V
Forward Transfer Admittance	$ y_{fs} $	$I_D=4\text{A}$, $V_{DS}=10\text{V}^*$	1.0	1.8	—	S
Input Capacitance	C_{iss}	$V_{DS}=10\text{V}$, $V_{GS}=0$ $f=1\text{MHz}$	—	750	—	pF
Output Capacitance	C_{oss}		—	300	—	pF
Reverse Transfer Capacitance	C_{rss}		—	60	—	pF
Turn-on Delay Time	$t_{d(on)}$	$I_D=2\text{A}$, $V_{GS}=15\text{V}$ $R_L=15\Omega$	—	15	—	ns
Rise Time	t_r		—	25	—	ns
Turn-off Delay Time	$t_{d(off)}$		—	70	—	ns
Fall Time	t_f		—	40	—	ns
Body-Drain Diode Forward Voltage	V_{DF}	$I_F=4\text{A}$, $V_{GS}=0$	—	0.9	—	V
Body-Drain Diode Reverse Recovery Time	t_{rr}	$I_F=4\text{A}$, $V_{GS}=0$ $di_F/dt=50\text{A}/\mu\text{s}$	—	300	—	ns

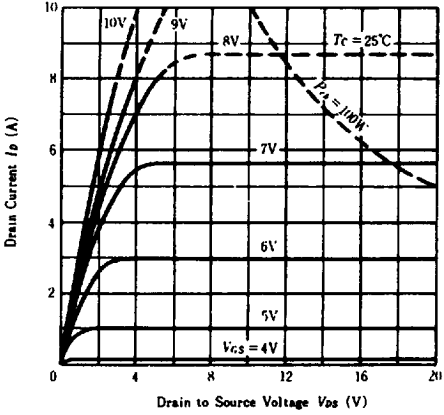
*Pulse Test

HITACHI/(OPTOELECTRONICS)

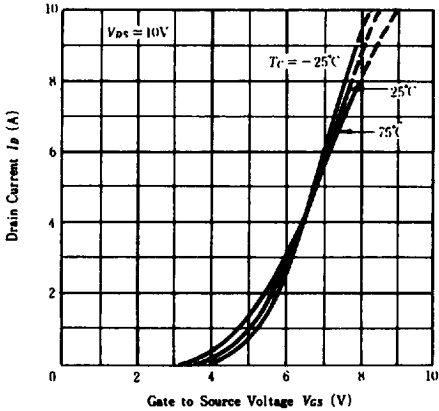
MAXIMUM SAFE OPERATION AREA



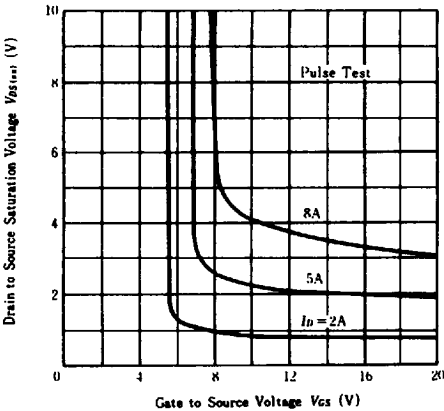
TYPICAL OUTPUT CHARACTERISTICS



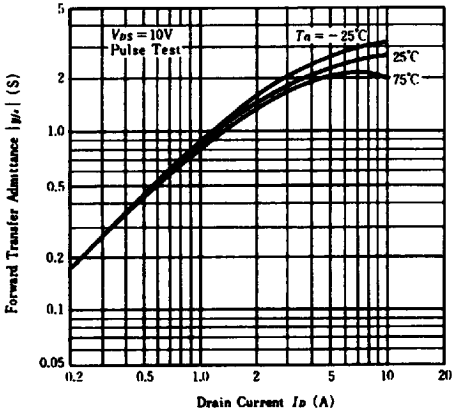
TYPICAL TRANSFER CHARACTERISTICS



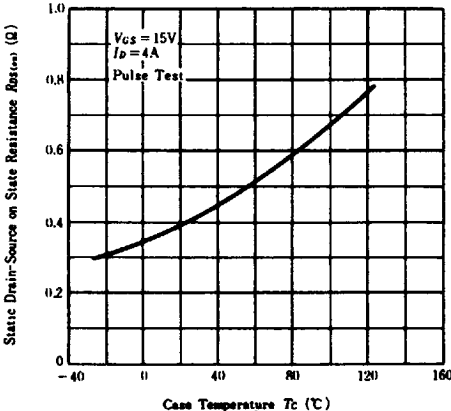
DRAIN-SOURCE SATURATION VOLTAGE VS. GATE-SOURCE VOLTAGE



FORWARD TRANSFER ADMITTANCE VS. DRAIN CURRENT

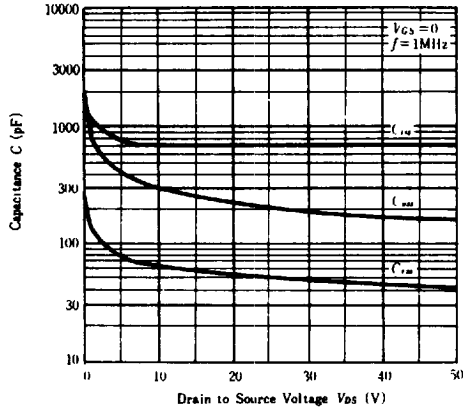


STATIC DRAIN-SOURCE ON STATE RESISTANCE VS. TEMPERATURE

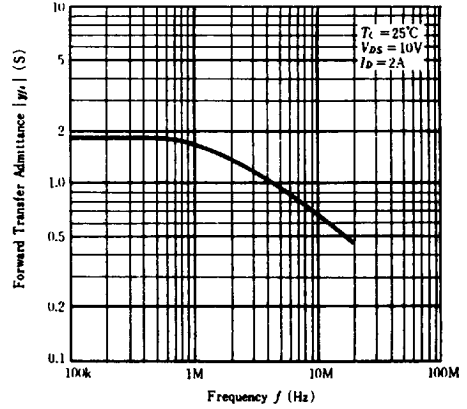


HITACHI/OPTOELECTRONIC

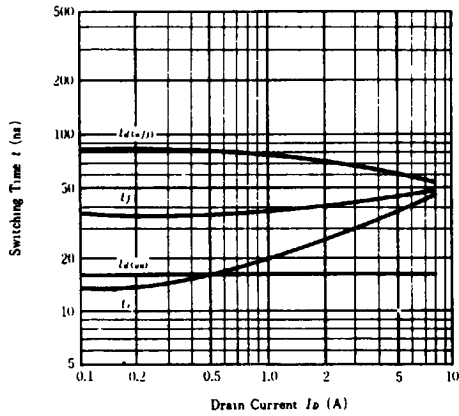
TYPICAL CAPACITANCE VS. DRAIN-SOURCE VOLTAGE



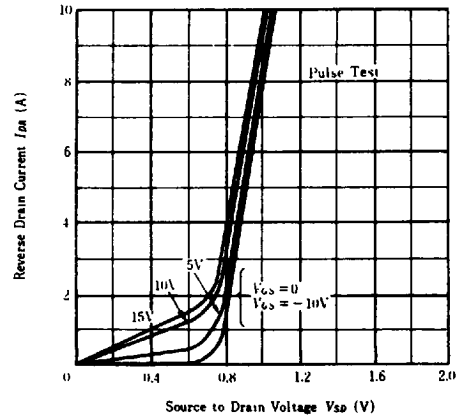
FORWARD TRANSFER ADMITTANCE VS. FREQUENCY



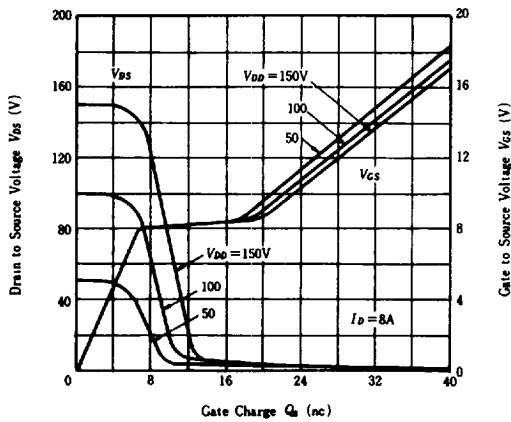
SWITCHING CHARACTERISTICS



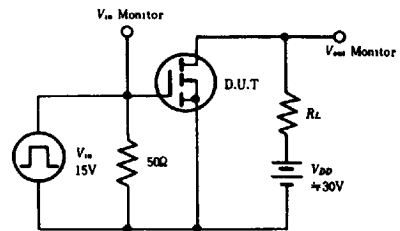
MAXIMUM BODY-DRAIN DIODE FORWARD VOLTAGE



DYNAMIC INPUT CHARACTERISTICS



SWITCHING TIME TEST CIRCUIT



WAVEFORMS

